

Supporting Information

Early-Transition-Metal Complexes of Functionalized Nonagermanide Clusters:

Synthesis and Characterization of $[\text{Cp}_2(\text{MeCN})\text{Ti}(\eta^1\text{-Ge}_9\{\text{Si}(\text{TMS})_3\}_3)]$

and $\text{K}_3[\text{Cp}_2\text{Ti}(\eta^1\text{-Ge}_9\{\text{Si}(\text{TMS})_3\}_2)_2]$

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Crystallographic Data

Table S1. Crystallographic data of compounds **1** and **2**.

compound	1	2
fw [g·mol ⁻¹]	1686.57	3145.25
space group	<i>P2₁/c</i>	<i>P2₁/c</i>
<i>a</i> [Å]	15.458(1)	42.249(1)
<i>b</i> [Å]	22.460(2)	36.427(1)
<i>c</i> [Å]	22.268(2)	18.0896(5)
α [deg]	90	90
β [deg]	95.176(6)	100.638(2)
γ [deg]	90	90
<i>V</i> [Å ³]	7700(11)	27362(1)
<i>Z</i>	4	8
<i>T</i> [K]	100(2)	100(2)
λ [Å]	0.7288	MoK α
ρ_{calcd} [g·cm ⁻³]	1.455	1.527
μ [mm ⁻¹]	3.771	4.208
<i>R</i> _{int} / <i>R</i> _{δ}	0.0771/0.0481	0.0497/0.0449
<i>R</i> ₁ [<i>I</i> > 2 σ (<i>I</i>) / all data]	0.0288/0.0426	0.0715/0.0891
<i>wR</i> ₂ [<i>I</i> > 2 σ (<i>I</i>) / all data]	0.0568/0.0622	0.1399/0.1455
goodness of fit	1.011	1.215
max./min. diff. el. density [e·Å ⁻³]	0.51/-0.40	2.35/-1.28

Table S2. Selected bond lengths and angles in compound **1**.

bond	distance [Å]
Ge1-Ge2	2.527(1)
Ge1-Ge4	2.527(1)
Ge1-Ge5	2.633(2)
Ge1-Ge8	2.651(2)
Ge2-Ge3	2.557(2)
Ge2-Ge5	2.598(1)
Ge2-Ge6	2.566(1)
Ge3-Ge4	2.567(1)
Ge3-Ge6	2.616(2)
Ge3-Ge7	2.657(2)
Ge4-Ge7	2.568(2)
Ge4-Ge8	2.615(1)
Ge5-Ge8	2.852(2)
Ge5-Ge9	2.514(1)
Ge6-Ge7	2.854(2)
Ge6-Ge9	2.518(2)
Ge7-Ge9	2.525(1)
Ge8-Ge9	2.512(1)
Ge2-Si1	2.405(2)
Ge4-Si2	2.413(2)
Ge9-Si3	2.371(2)
Ge1-Ti	2.767(2)
Ti-Ct1*	2.049(1)
Ti-Ct2*	2.045(1)
Ge7-Ge8 (h ₁)	3.053(3)
Ge5-Ge6 (h ₂)	3.077(3)
Ge1-Ge3 (h ₃)	3.812(3)
atoms	angle [deg]
Ct1-Ti-Ct2*	135.34(5)
Ge1-Ti-N	84.59(3)

*Ct: centroids of Cp rings; Ct1: C1-C5; Ct2: C6-C10

Table S3. Selected bond lengths and angles in **2a-I**.

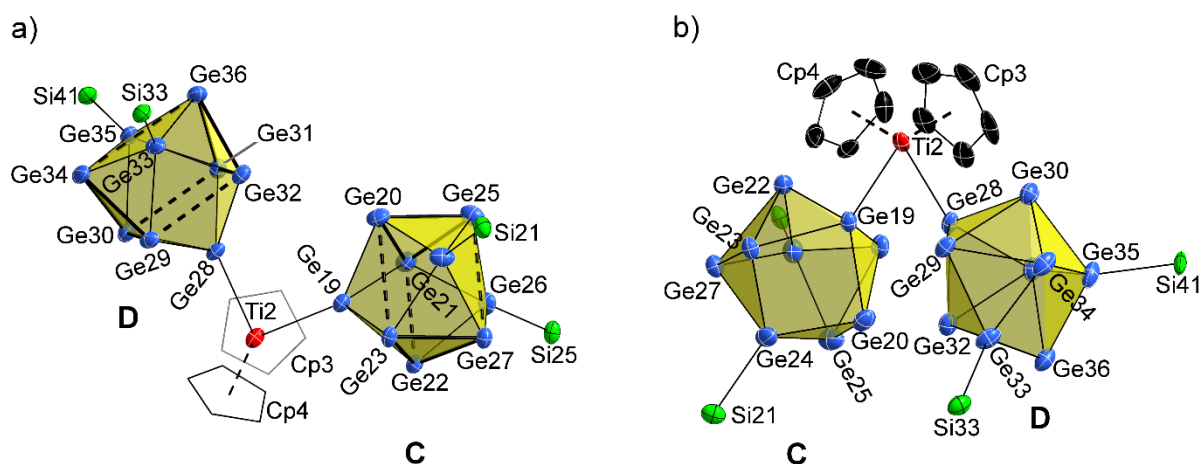
bond	distance [Å]	bond	distance [Å]
Ge1-Ge2	2.583(1)	Ge10-Ge11	2.584(1)
Ge1-Ge3	2.558(1)	Ge10-Ge12	2.577(1)
Ge1-Ge4	2.561(1)	Ge10-Ge13	2.577(1)
Ge1-Ge5	2.546(1)	Ge10-Ge14	2.583(1)
Ge2-Ge3	2.715(2)	Ge11-Ge12	2.666(1)
Ge2-Ge6	2.595(1)	Ge11-Ge15	2.544(1)
Ge2-Ge7	2.641(1)	Ge11-Ge16	2.591(1)
Ge3-Ge7	2.672(1)	Ge12-Ge16	2.715(1)
Ge3-Ge8	2.553(1)	Ge12-Ge17	2.536(1)
Ge4-Ge7	2.657(2)	Ge13-Ge14	2.673(1)
Ge4-Ge8	2.560(2)	Ge13-Ge17	2.551(1)
Ge4-Ge9	2.638(1)	Ge13-Ge18	2.728(1)
Ge5-Ge6	2.546(1)	Ge14-Ge15	2.545(1)
Ge5-Ge9	2.683(1)	Ge14-Ge18	2.599(1)
Ge6-Ge7	2.531(1)	Ge15-Ge16	2.574(1)
Ge6-Ge9	2.529(1)	Ge15-Ge18	2.542(1)
Ge7-Ge8	2.523(1)	Ge16-Ge17	2.534(2)
Ge8-Ge9	2.539(1)	Ge17-Ge18	2.497(1)
Ge6-Si1	2.387(2)	Ge15-Si9	2.381(2)
Ge8-Si5	2.386(2)	Ge17-Si13 / Ge17-Si17	2.311(6) / 2.486(8)
Ge1-Ti1	2.714(2)	Ge10-Ti1	2.739(2)
Ti1-Ct1*	2.051(2)	Ti1-Ct2*	2.055(1)
Ge2-Ge5 (h ₁)	3.018(1)	Ge12-Ge13 (h ₁)	2.967(1)
Ge3-Ge4 (h ₂)	3.069(1)	Ge11-Ge14 (h ₂)	3.468(1)
Ge7-Ge9 (h ₃)	3.788(1)	Ge16-Ge18 (h ₃)	3.576(1)
atoms	angle [deg]	atoms	angle [deg]
Ct1-Ti1-Ct2*	134.00(2)	Ge1-Ti1-Ge10	83.83(2)

*Ct: centroids of Cp rings; Ct1: C1-C5; Ct2: C6-C10

Table S4. Selected bond lengths and angles in **2a-II**.

bond	distance [Å]	bond	distance [Å]
Ge19-Ge20	2.576(1)	Ge28-Ge29	2.556(1)
Ge19-Ge21	2.585(1)	Ge28-Ge30	2.573(1)
Ge19-Ge22	2.579(1)	Ge28-Ge31	2.547(1)
Ge19-Ge23	2.585(1)	Ge28-Ge32	2.572(1)
Ge20-Ge21	2.670(1)	Ge29-Ge30	2.730(1)
Ge20-Ge24	2.544(1)	Ge29-Ge33	2.559(1)
Ge20-Ge25	2.596(2)	Ge29-Ge34	2.687(1)
Ge21-Ge25	2.709(1)	Ge30-Ge34	2.646(1)
Ge21-Ge26	2.539(1)	Ge30-Ge35	2.586(1)
Ge22-Ge23	2.660(1)	Ge31-Ge32	2.747(1)
Ge22-Ge26	2.554(1)	Ge31-Ge35	2.546(1)
Ge22-Ge27	2.735(1)	Ge31-Ge36	2.673(1)
Ge23-Ge24	2.550(1)	Ge32-Ge33	2.567(1)
Ge23-Ge27	2.592(1)	Ge32-Ge36	2.626(1)
Ge24-Ge25	2.583(1)	Ge33-Ge34	2.521(1)
Ge24-Ge27	2.545(1)	Ge33-Ge36	2.552(1)
Ge25-Ge26	2.539(1)	Ge34-Ge35	2.517(1)
Ge26-Ge27	2.492(1)	Ge35-Ge36	2.540(1)
Ge24-Si21	2.385(3)	Ge33-Si33	2.395(3)
Ge26-Si25 / Ge26-Si29	2.423(8) / 2.358(8)	Ge35-Si37 / Ge35-Si41	2.475(8) / 2.289(9)
Ge19-Ti2	2.732(2)	Ge28-Ti2	2.725(2)
Ti2-Ct3*	2.049(1)	Ti2-Ct4*	2.063(1)
Ge21-Ge22 (h ₁)	2.981(1)	Ge30-Ge31 (h ₁)	3.020(1)
Ge20-Ge23 (h ₂)	3.486(1)	Ge29-Ge32 (h ₂)	3.042(1)
Ge25-Ge27 (h ₃)	3.558(1)	Ge34-Ge36 (h ₃)	3.797(1)
atoms	angle [deg]	atoms	angle [deg]
Ct3-Ti2-Ct4*	133.91(2)	Ge19-Ti2-Ge28	83.52(2)

*Ct: centroids of Cp rings; Ct1: C56-C60; Ct2: C61-C65



EPR Data

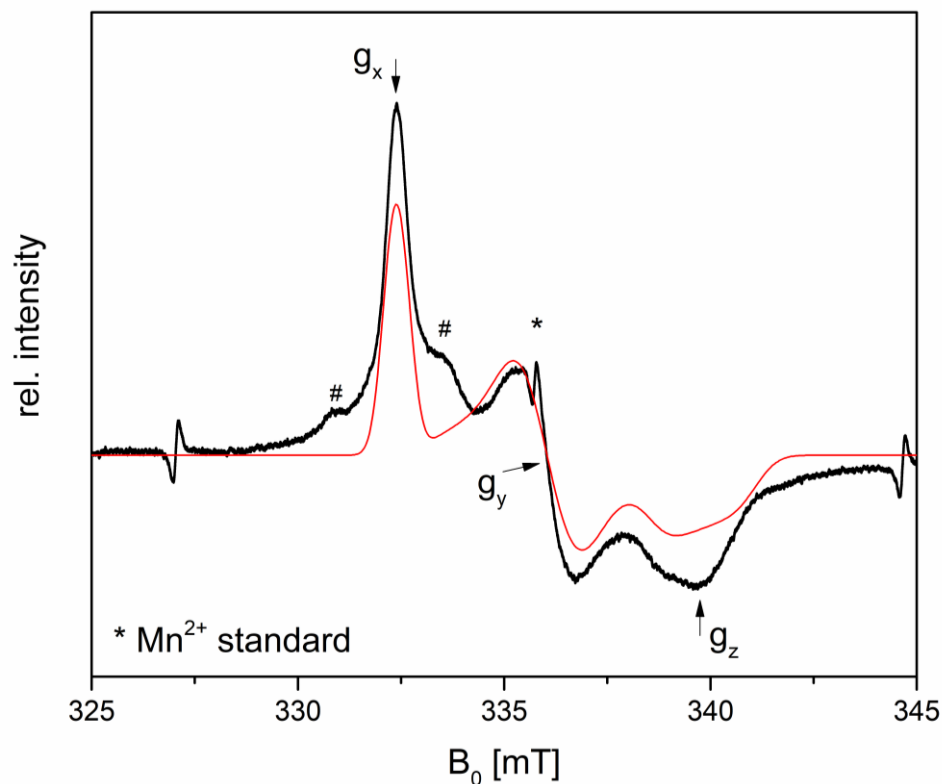


Figure S2. Experimental (black) and simulated (red) X-Band EPR spectrum of compound **2** in frozen thf solution at 130 K. The values for the anisotropic g-factors g_x : 1.992; g_y : 1.970 and g_z : 1.942 were determined relative to an Mn^{2+} standard (phase inverted, labelled with *), and simulated. The average g-factor was calculated to $g_{avg} = 1.968$. The shoulders labelled with # are probably caused by a minor impurity.

ESI-MS Data

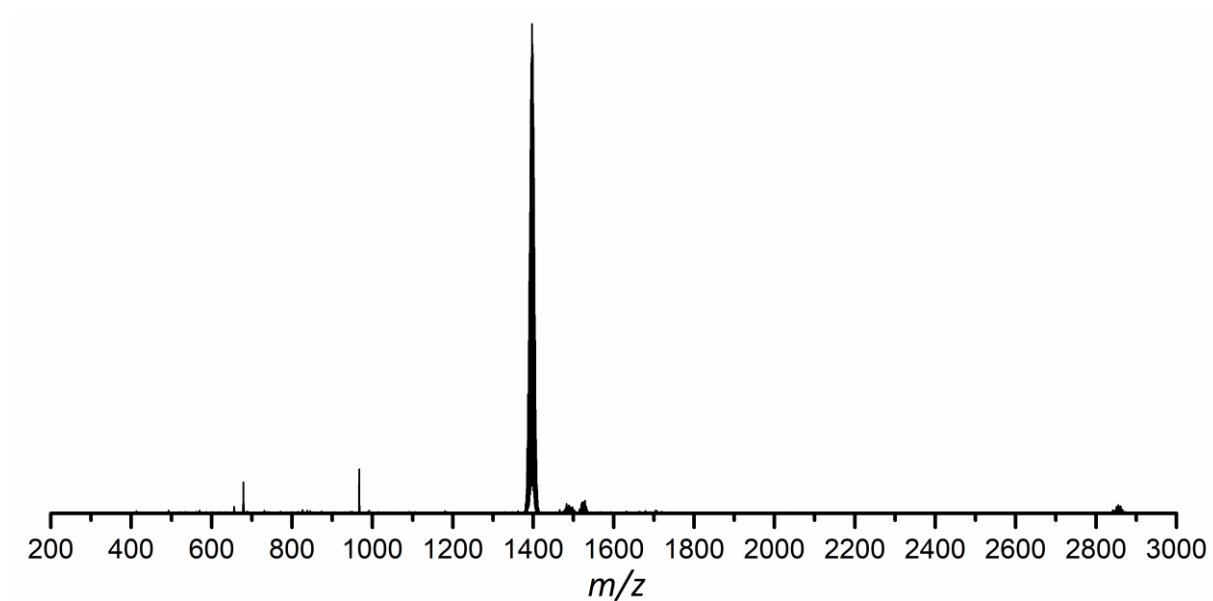


Figure S3. ESI-MS spectrum obtained from an aliquot sample of a thf solution of diluted crystals of **1**. The signal at m/z 1396.8 can be assigned to $\{[\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_3]\}^+$ formed upon cleavage of the $[\text{Cp}_2\text{Ti}(\text{MeCN})]^+$ moiety from **1** during the ionization process.

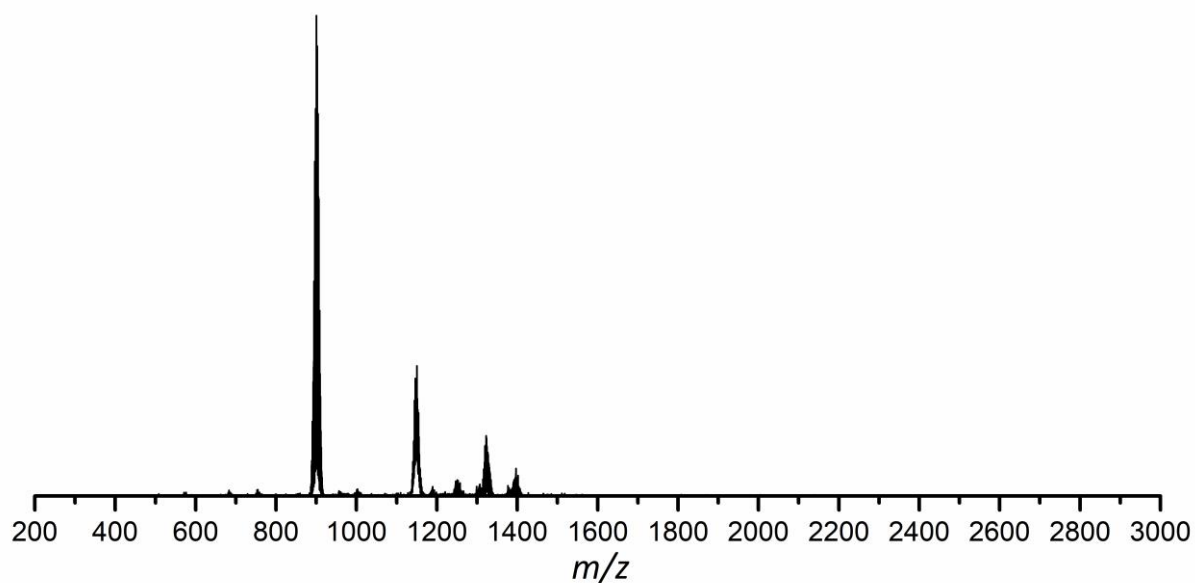


Figure S4. ESI-MS spectrum of an aliquot sample of a thf solution of diluted crystals of compound **2**. The signal at m/z 1326.5 can be assigned to $\{[\text{Cp}_2\text{Ti}(\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_2)]\}^+$ formed upon cleavage of one bis-silylated $[\text{Ge}_9]$ cluster ligand from **2a**. Besides the signal assigned to the Ge_9 -Ti compound signals at m/z 900.4 and m/z 1147.4 appeared which can be assigned to $[\text{Ge}_9]$ clusters $\{[\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_1]\}^+$ or $\{[\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_2]\}^+$ formed upon further fragmentation of $\{[\text{Cp}_2\text{Ti}(\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_2)]\}^+$ during the ionization process.

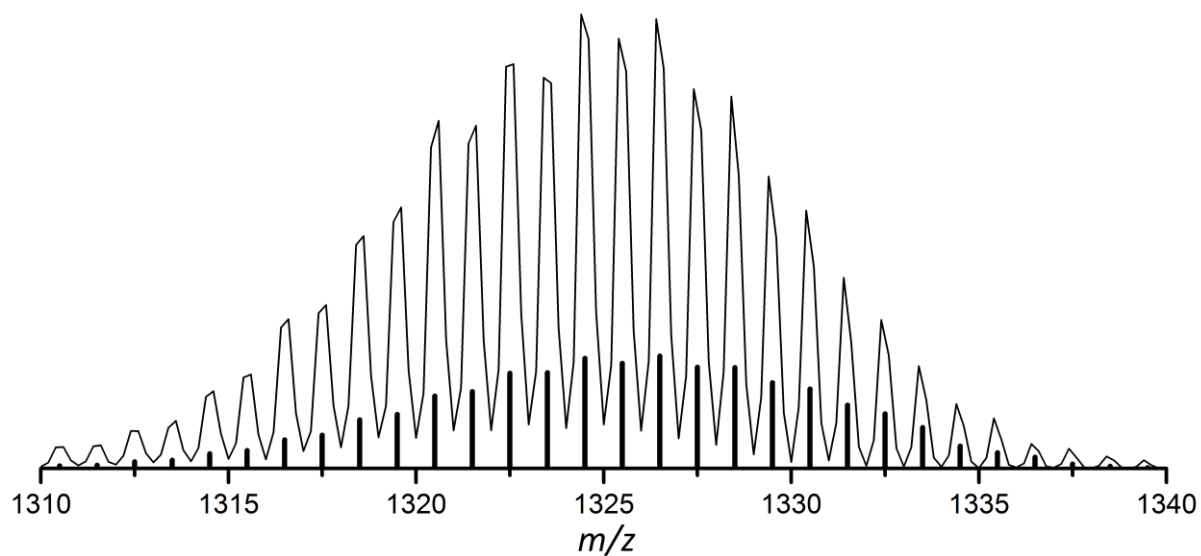


Figure S5. Detail view of the ESI-MS signal at m/z 1326.5, which can be assigned to $\{[\text{Cp}_2\text{Ti}(\text{Ge}_9\{\text{Si}(\text{TMS})_3\}_2)]\}^+$. The signal was monitored upon measurement of an aliquot sample of a diluted thf solution of crystals of compound **2**. The calculated pattern is shown as black bars.